## **TEC-201**

## B. TECH. (SECOND SEMESTER) END SEMESTER EXAMINATION, 2019 (ALL BRANCHES)

BASIC ELECTRONICS ENGINEERING

Time: Three Hours
Maximum Marks: 100

- Note:(i) This question paper contains five questions.
  - (ii) All questions are compulsory.
  - (iii) Instructions on how to attempt a question are mentioned against it.
  - (iv) Total marks assigned to each question are twenty.
- Attempt any two questions of choice from (a),
   (b) and (c). (2×10=20 Marks)
  - (a) Discuss laws of Boolean algebra in detail.
  - (b) Perform the following number system conversion:
    - (i)  $(43)_{10} = (?)_2$
    - (ii)  $(59)_{10} = (?)_{BCD}$
    - (iii)  $(13)_8 = (?)_2$
    - (iv)  $(11011001)_2 = (?)_{16}$ 
      - (v)  $(AC)_{16} = (?)_{10}$

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- (c) Perform the following:
  - (i)  $(38)_{10} (25)_{10}$  in Binary using 1's complement
  - (ii)  $(29)_{10} (34)_{10}$  in Binary using 2's complement
- 2. Attempt any two questions of choice from (a), (2×10=20 Marks) (b) and (c).
  - (a) Derive the continuity equation for semiconductors.
  - (b) Differentiate between insulators, semiconductors and conductors in detail.
  - (c) Write short notes on the following:
    - (i) P type semiconductors
    - (ii) Current density

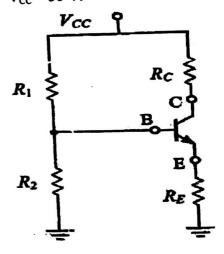
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- 3. Attempt any two questions of choice from (a), (2×10=20 Marks) (b) and (c).
  - (a) What do you mean by the depletion layer of a PN junction diode? Compare V-I characteristics of Silicon and Germanium diodes.
  - (b) Discuss the working of a center tapped full wave rectifier and derive its rectification efficiency.
  - (c) The reverse saturation current at 300 K of a p-n junction Ge diode is 5  $\mu$ A. Find voltage to be applied across the diode to obtain a forward current of 8 mA. Also determine its static and dynamic resistance.

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- 4. Attempt any two questions of choice from (a), (2×10=20 Marks) (b) and (c).
  - (a) Derive the mathematical relation between current gains α and β of a BJT. Also discuss the leakage currents I<sub>CBO</sub> and I<sub>CEO</sub>.
  - (b) Discuss the construction, operation and characteristics of E-MOSFET.
  - (c) Consider the following voltage divider bias circuit of BJT. Determine the collector current I<sub>C</sub> and collector to emitter voltage  $V_{CE}$ . Given,  $R_1 = 60 \text{ k}\Omega$ ,  $R_2 =$ 7  $k\Omega$ ,  $R_C = 12 k\Omega$ ,  $R_E = 1.7 k\Omega$ ,  $V_{BE} = 0.7 \text{ V, current gain } \beta = 50 \text{ and}$  $V_{CC} = 30 \text{ V}.$



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- 5. Attempt any two questions of choice from (a), (b) and (c). (2×10=20 Marks)
  - (a) Write characteristics of an ideal Op-Amp. Also discuss the concept of virtual ground.
  - (b) Draw neat circuit diagrams and derive the output of the following Op-Amp based circuits:
    - (i) Adder
    - (ii) Subtractor
  - (c) What do you mean by an inverting amplifier? Discuss, how an Op-Amp can be used as a differentiator?